

CLAIMS

Sub B2 1. A method of manufacture of a semiconductor device, comprising the steps of:

5 providing an adhesive between a surface of a semiconductor chip having a plurality of electrodes on which said electrodes are provided and a surface of a substrate having a plurality of leads formed on which said leads are formed;

10 positioning at least one of said plurality of electrodes to oppose at least one of said plurality of leads; and

15 applying pressure in a direction such as to make a gap between said semiconductor chip and said substrate narrower;

20 wherein on the surface of said substrate on which said leads are formed, in a region being at least part of a region of adherence of said semiconductor chip, a film is formed with a lower adhesion to said adhesive than a base material of said substrate.

WUEI 2. The method of manufacture of a semiconductor device as defined in claim 1,

25 wherein said adhesive is formed of an anisotropic conductive material having conductive particles dispersed in an insulating material.

3. The method of manufacture of a semiconductor device as defined in claim 1,

wherein said leads and said film are formed by etching a conductive foil adhered to said base material of said substrate.

4. The method of manufacture of a semiconductor device as defined in claim 1,

wherein a conductive foil used when forming said leads is also used to form said film.

5. The method of manufacture of a semiconductor device as defined in claim 4,

wherein said film is formed simultaneously with said leads.

6. The method of manufacture of a semiconductor device as defined in claim 1,

wherein said electrodes are provided on an extremity of said surface of said semiconductor chip; and

wherein said film is formed in a region opposing a central part of said surface of said semiconductor chip.

7. The method of manufacture of a semiconductor device as defined in <sup>Claim 1</sup> ~~any of claims 1 to 6~~,

wherein said film is formed to spread two-dimensionally, with at least one opening exposing a surface

of said substrate.

8. The method of manufacture of a semiconductor device  
as defined in ~~any of claims 1 to 6,~~

5 wherein said film is formed to project outside a  
region in which said semiconductor chip is adhered.

9. The method of manufacture of a semiconductor device  
as defined in ~~any of claims 1 to 6,~~

10 wherein said film is formed to be symmetrical about a  
center point of a region in which said semiconductor chip  
is adhered.

10. The method of manufacture of a semiconductor device  
as defined in ~~any of claims 1 to 6,~~

15 wherein said film is formed to avoid at least one of  
said leads.

11. The method of manufacture of a semiconductor device  
as defined in ~~any of claims 1 to 6,~~

20 wherein a part of said film is formed in a position  
overlying said electrodes.

12. A semiconductor device comprising:

25 a semiconductor chip having a plurality of  
electrodes;

a substrate on which is formed a plurality of leads;

and

an adhesive provided between a surface of said semiconductor chip on which said electrodes are formed and a surface of said substrate on which said leads are formed, and adhering said semiconductor chip and said substrate,

wherein at least one of said plurality of electrodes and at least one of said plurality of leads are electrically connected; and

wherein on said substrate in a region including at least a part of a region opposing said semiconductor chip, a film is formed with a lower adhesion to said adhesive than a base material of said substrate.

13. The semiconductor device as defined in claim 12, wherein said adhesive is formed of an anisotropic conductive material having conductive particles dispersed in an insulating material.

14. The semiconductor device as defined in claim 12, wherein said leads and said film are formed of the same electrically conductive material.

15. The semiconductor device as defined in claim 12, wherein said electrodes are provided at an extremity of said surface of said semiconductor chip; and

wherein said film is formed in a region opposing a central part of said surface of said semiconductor chip.

16. The semiconductor device as defined in ~~any of claims~~ <sup>Claim 12</sup>  
~~12 to 15,~~

wherein said film is formed to spread two-  
5 dimensionally, with at least one opening exposing a surface  
of said substrate.

17. The semiconductor device as defined in ~~any of claims~~ <sup>Claim 12</sup>  
~~12 to 15,~~

10 wherein said film is formed to project outside a  
region in which said semiconductor chip is adhered.

18. The semiconductor device as defined in ~~any of claims~~ <sup>Claim 12</sup>  
~~12 to 15,~~

15 wherein said film is formed to be symmetrical about a  
center point of a region in which said semiconductor chip  
is adhered.

19. The semiconductor device as defined in ~~any of claims~~ <sup>Claim 12</sup>  
20 ~~12 to 15,~~

wherein said film is formed to avoid at least one of  
said leads.

20. The ~~method of manufacture of a~~ semiconductor device  
25 as defined in ~~any of claims 12 to 15,~~ <sup>Claim 12</sup>

wherein a part of said film is formed in a position  
overlying said electrodes.

21. A circuit board on which is mounted the semiconductor device as defined in ~~any of claims 12 to 15.~~ <sup>Claim 12</sup>

22. An electronic instrument having the semiconductor device as defined in ~~any of claims 12 to 15.~~ <sup>Claim 12</sup>

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